

# HUFA76439S3S-VB Datasheet N-Channel 60-V (D-S) MOSFET

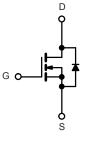
PRODUCT SUMMARY		
V <sub>DS</sub>	60	V
$R_{DS(on)}$ $V_{GS} = 10$ V	11	mΩ
$R_{DS(on)}$ $V_{GS} = 4.5$ V	12	mΩ
I <sub>D</sub>	75	А
Configuration	Sin	gle

#### FEATURES

- 175 °C Junction Temperature
- Trench Power MOSFET







N-Channel MOSFET

Parameter		Symbol	Limit	Unit	
Gate-Source Voltage	V <sub>GS</sub>	± 20	V		
Continuous Drain Current (T <sub>1</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 25 °C	L	75		
Continuous Drain Current $(T_J = 175 \text{ C})^{\circ}$	T <sub>C</sub> = 100 °C	ID -	50 <sup>a</sup>		
Pulsed Drain Current	I <sub>DM</sub>	200	А		
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	50 <sup>a</sup>			
Avalanche Current	I <sub>AS</sub>	50	-		
Single Avalanche Energy (Duty Cycle $\leq$ 1 %) L = 0.1 mH		E <sub>AS</sub>	125	mJ	
Maximum Dawar Dissinction	T <sub>C</sub> = 25 °C	P <sub>D</sub>	136	w	
Maximum Power Dissipation	T <sub>A</sub> = 25 °C		3 <sup>b</sup> , 8.3 <sup>b, c</sup>	v	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Typical	Maximum	Unit			
Maximum lunction to Ambienta	$t \le 10 \text{ sec}$	P	15	18			
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	R <sub>thJA</sub>	40	50	°C/W		
Maximum Junction-to-Case		R <sub>thJC</sub>	0.85	1.1			
Notes:				•			

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c.  $t \leq$  10 s.



Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit		
Static								
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS}$ = 0 V, I <sub>D</sub> = 250 µA	60			V		
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1		3	v		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ± 20 V			± 100	nA		
		$V_{DS}$ = 60 V, $V_{GS}$ = 0 V			1			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ = 60 V, $V_{GS}$ = 0 V, $T_{J}$ = 125 °C			50	Per 1		
		$V_{DS}$ = 60 V, $V_{GS}$ = 0 V, $T_{J}$ = 175 °C			250			
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	60			Α		
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.011				
Drain-Source On-State Resistance <sup>b</sup>	Б	$V_{GS}$ = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C		0.016		Ω		
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C		0.020				
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 15 A		0.012				
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		60		S		
Dynamic								
Input Capacitance	C <sub>iss</sub>			4300				
Output Capacitance	C <sub>oss</sub>	$V_{GS}$ = 0 V, $V_{DS}$ = 25 V, f = 1 MHz		470		pF		
Reverse Transfer Capacitance	C <sub>rss</sub>			225		1		
Total Gate Charge <sup>c</sup>				47				
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{\rm DS}$ = 30 V, $V_{\rm GS}$ = 10 V, $I_{\rm D}$ = 50 A		10		nC		
Gate-Drain Charge <sup>c</sup> Q				12				
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			10	20			
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 30 V, $R_L$ = 0.6 $\Omega$		15	25			
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$\text{I}_\text{D}{\cong}50$ A, $\text{V}_\text{GEN}$ = 10 V, Rg = 2.5 $\Omega$		35	50	ns		
Fall Time <sup>c</sup>	t <sub>f</sub>			20	30			
Source-Drain Diode Ratings and Cha	racteristics (	T <sub>C</sub> = 25 °C)		·	I			
Pulsed Current	I <sub>SM</sub>				60	А		
Diode Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		1	1.5	V		
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20 A, di/dt = 100 A/μs		45	100	ns		

Notes:

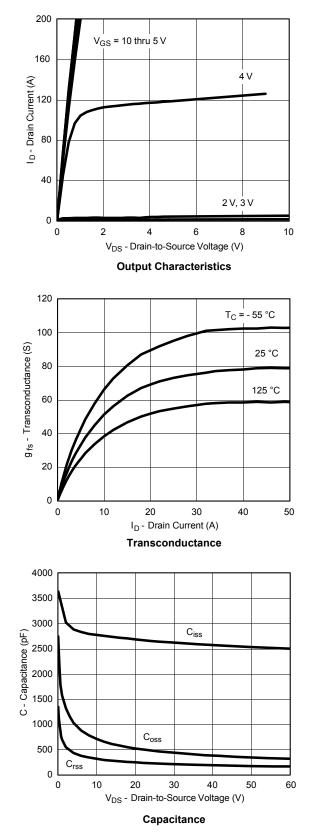
a. For design aid only; not subject to production testing. b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

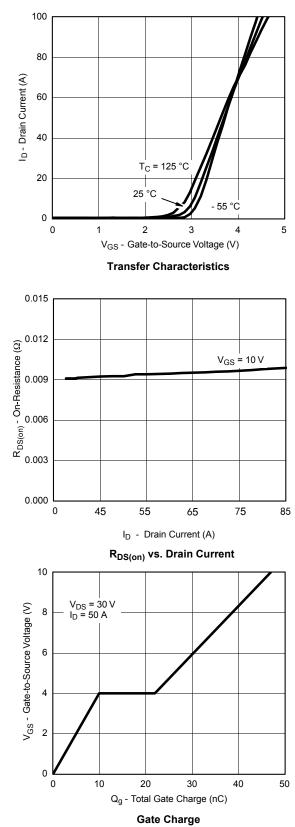
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



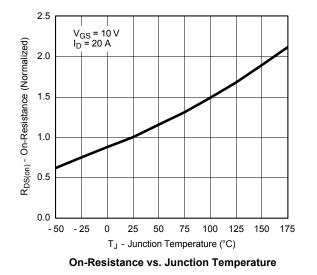




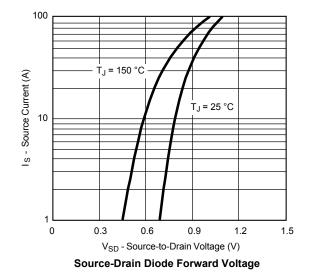


服务热线:400-655-8788



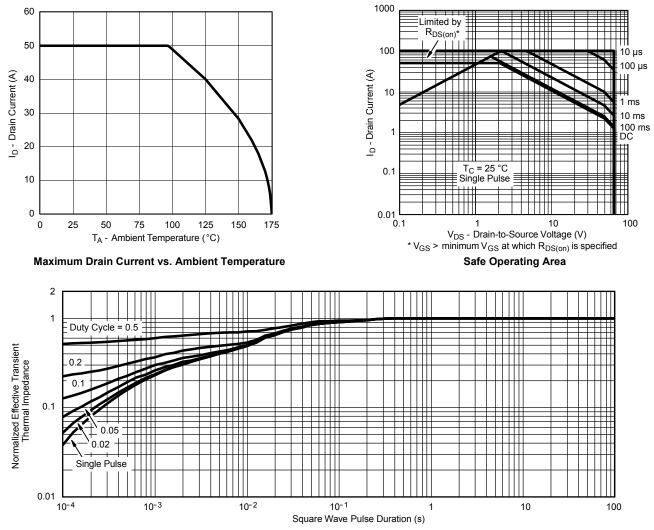


#### TYPICAL CHARACTERISTICS (25 °C unless noted)





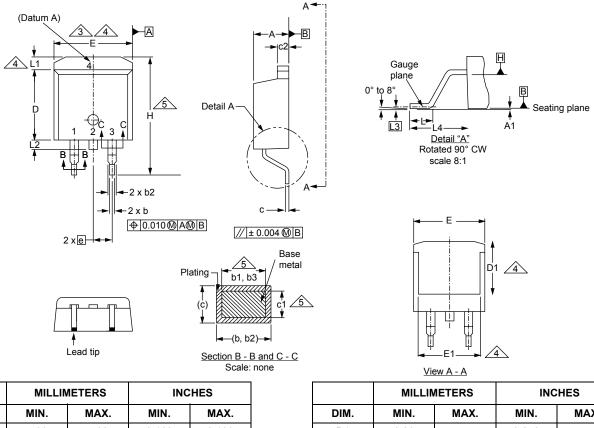
#### **THERMAL RATINGS**



Normalized Thermal Transient Impedance, Junction-to-Case



#### **TO-263AB (HIGH VOLTAGE)**



	MILLIMETERS		INCHES		DIM.	MILLIMETERS		INCHES	
DIM.	DIM. MIN. MAX. MIN. MAX.	MAX.	MIN.	MAX.		MIN.	М		
А	4.06	4.83	0.160	0.190	D1	6.86	-	0.270	
A1	0.00	0.25	0.000	0.010	E	9.65	10.67	0.380	0.
b	0.51	0.99	0.020	0.039	E1	6.22	-	0.245	
b1	0.51	0.89	0.020	0.035	е	2.54 BSC		0.100	BSC
b2	1.14	1.78	0.045	0.070	Н	14.61	15.88	0.575	0.
b3	1.14	1.73	0.045	0.068	L	1.78	2.79	0.070	0.
С	0.38	0.74	0.015	0.029	L1	-	1.65	-	0.
c1	0.38	0.58	0.015	0.023	L2	-	1.78	-	0.
c2	1.14	1.65	0.045	0.065	L3	0.25 BSC		0.010	BSC
D	8.38	9.65	0.330	0.380	L4	4.78	5.28	0.188	0.

Notes

- 4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
- 5. Dimension b1 and c1 apply to base metal only.

6. Datum A and B to be determined at datum plane H.

7. Outline conforms to JEDEC outline to TO-263AB.

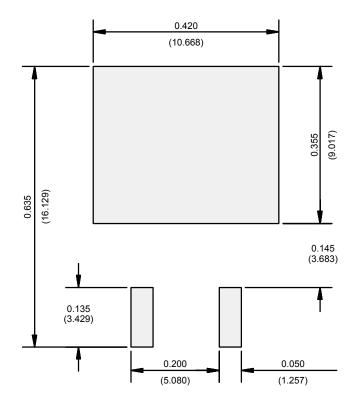
<sup>1.</sup> Dimensioning and tolerancing per ASME Y14.5M-1994.

<sup>2.</sup> Dimensions are shown in millimeters (inches).

Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.



#### **RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads Dimensions in Inches/(mm)



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